

1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

1. General description

Ultrafast, epitaxial rectifier diode in a SOD59 (TO-220AC) plastic package

2. Features and benefits

- · Fast switching
- Low thermal resistance
- · Soft recovery characteristic
- · Low forward voltage drop
- · Low switching loss
- High thermal cycling performance

3. Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	Square-wave; δ = 1.0	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 108 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	15	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_{mb} \le 108$ °C; Square-wave	-	-	30	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; Sinusoidal waveform; Fig. 4	-	-	130	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; Sinusoidal waveform	-	-	143	А
Static charact	teristics					
V_{F}	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1	1.2	V
		I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.17	1.38	V
Dynamic char	racteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $\frac{\text{Fig. 7}}{}$	-	50	60	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A 001aaa020
2	Α	anode		001aaa020
mb	mb	mounting base; cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYT79-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	Square-wave; δ = 1.0	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 108 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 108 °C; Square-wave	-	30	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; Sinusoidal waveform; <u>Fig. 4</u>	-	130	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; Sinusoidal waveform	-	143	Α
T _{stg}	storage temperature		-55	150	°C
T _j	junction temperature		-	150	°C

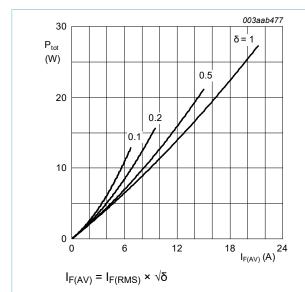


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

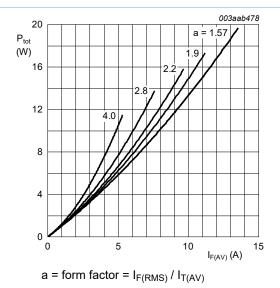


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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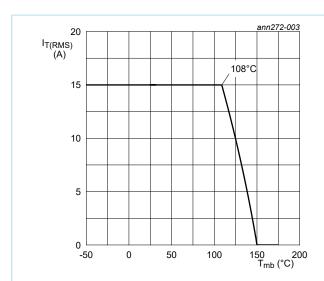


Fig. 3. RMS on-state current as a function of mounting base temperature; maximum values

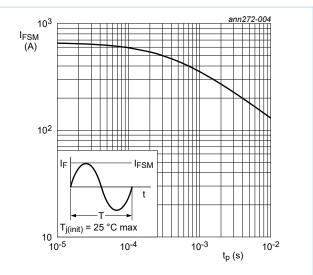


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air		-	60	-	K/W

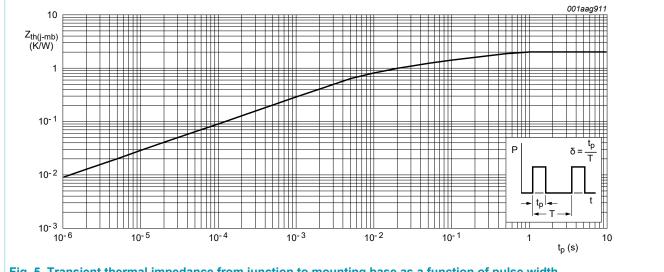


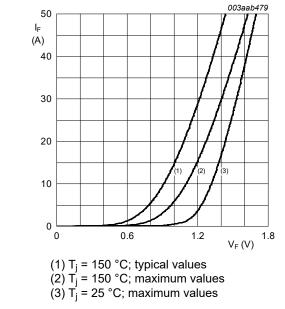
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			,		,
V _F	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1	1.2	V
		I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.17	1.38	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	5	50	μΑ
		V _R = 600 V; T _j = 100 °C	-	0.2	0.8	mA
Dynamic ch	aracteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; Fig. 7	-	40	70	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	50	60	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; \underline{\text{Fig. 7}}$	-	3	5.2	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}; Fig. 8$	-	3.2	-	V



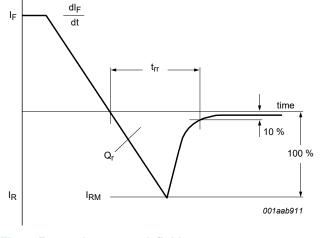
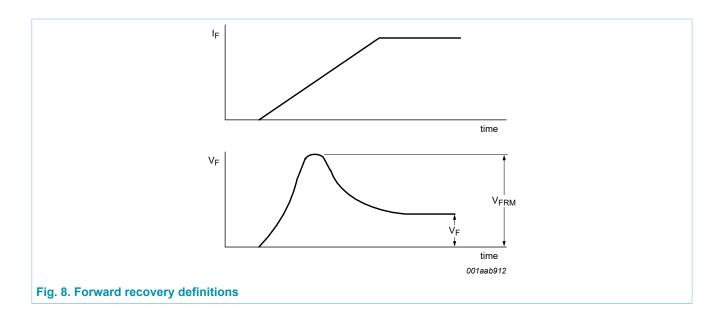


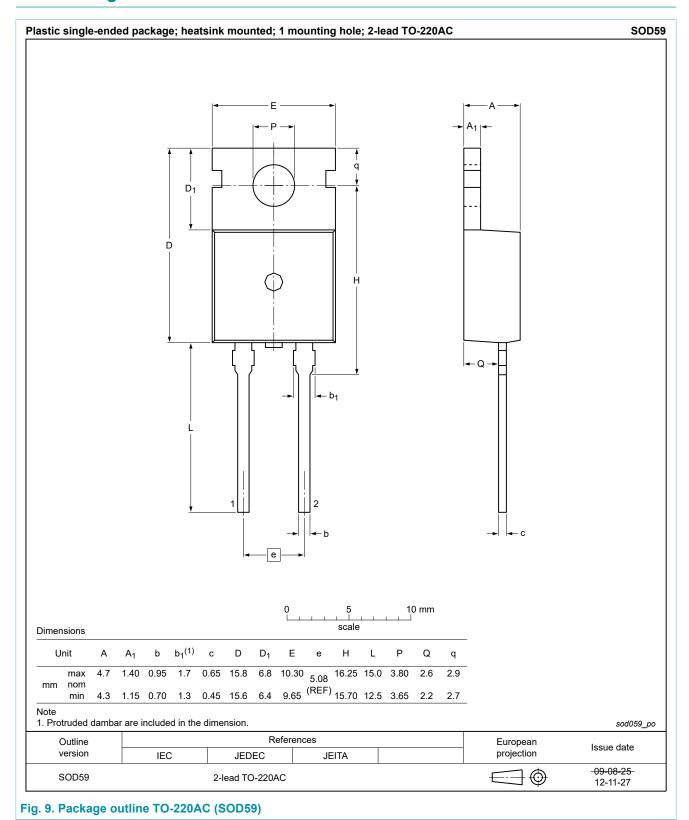
Fig. 7. Forward recovery definitions

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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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